

#### Description

The SI9926CDY-T1-GE3 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

### **General Features**

 $V_{DS} = 20V I_D = 8 A$  $R_{DS(ON)} < 20m\Omega @ V_{GS} = 4.5V$ 

### Application

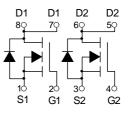
Battery protection

Load switch

Uninterruptible power supply







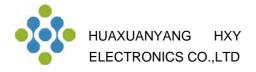
### **Dual N-Channel MOSFET**

### Package Marking and Ordering Information

<u> </u>	0		
Product ID	Pack	Brand	Qty(PCS)
SI9926CDY-T1-GE3	SOP-8	HXY MOSFET	3000

### Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
Vds	Drain-Source Voltage	20	V
Vgs	Gate-Source Voltage	±12	V
ID	Drain Current-Continuous	8	А
Ідм	Pulsed Drain Current	28	А
PD	Maximum Power Dissipation	2.25	W
Тј,Тѕтб	Operating Junction and Storage Temperature Range	-55 To 150	°C
Rejc	Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	80	°C <b>/W</b>



Dual N-Channel Enhancement Mode MOSFET

# Electrical Characteristics (TJ=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS} = 0V, I_D = 250 \mu A$	20	-	-	V
Gate Leakage Current	lgss	$V_{GS}$ = ±12V, $V_{DS}$ = 0V	-	-	±100	nA
Drain Cut-off Current	ldss	$V_{DS} = 20V, V_{GS} = 0V$	-	-	1	μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250µA	0.45	0.7	1	V
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> =5A	-	13	20	mΩ
Drain-Source On-State Resistance <sup>3</sup>	RDS(on)	$V_{GS}$ = 2.5V, I <sub>D</sub> = 4.7A	-	18	30	
		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 4.3A	-	28	57	
Dynamic Characteristics <sup>4</sup>	1	•	1	1	1	
Input Capacitance	Ciss		-	700	-	pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 10V, f = 1MHz	-	120	-	
Reverse Transfer Capacitance	Crss		-	105	-	
Switching Characteristics <sup>4</sup>		1	1	1		
Total Gate Charge	Qg		-	10.5	-	nC
Gate-Source Charge	Qgs	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 5A	-	2	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	2.5	-	
Turn-On Time	td(on)	V <sub>GS</sub> = 5V, V <sub>DD</sub> = 10V, I <sub>D</sub> = 5A,R <sub>G</sub> = 3Ω,	-	10	-	ns
Rise Time	tr		-	20	-	
Turn-Off Time	td(off)		-	32	_	
Fall Time	tr		-	12	_	
Source-Drain Diode Characterist	ics	1	1	1	1	
Body Diode Voltage <sup>3</sup>	Vsd	I <sub>S</sub> =4A, V <sub>GS</sub> = 0V	-	-	1.2	V
Continuous Source Current	Is		-	-	8	А

#### Notes:

1. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}$ =150°C.

2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.

3. Pulse Test: Pulse width≤300µs, duty cycle≤2%.

4. This value is guaranteed by design hence it is not included in the production test.



# SI9926CDY-T1-GE3 Dual N-Channel Enhancement Mode MOSFET

## **Typical Characteristics**

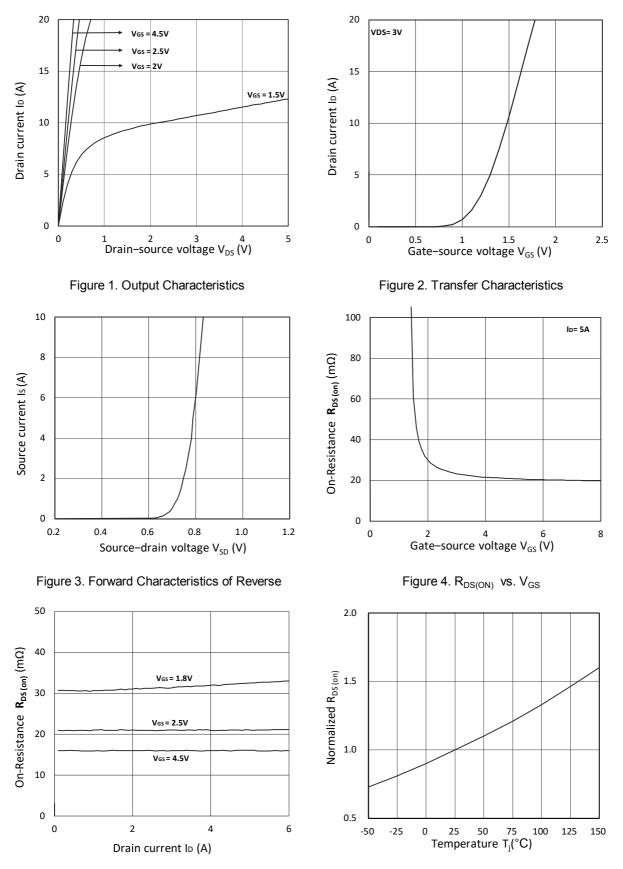
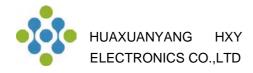


Figure 5.  $R_{DS(ON)}$  vs.  $I_D$ 



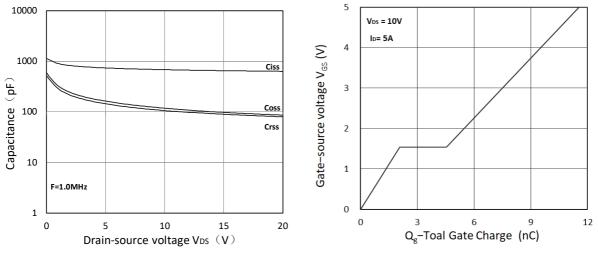
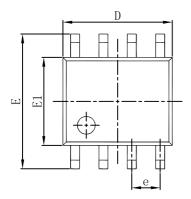


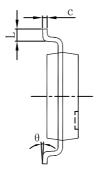
Figure 7. Capacitance Characteristics

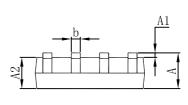
Figure 8. Gate Charge Characteristics



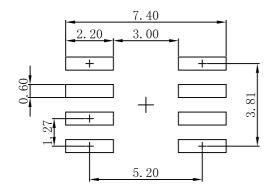
## **SOP-8 Package Outline Dimensions**







Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
с	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0.197	
e	1.270 (BSC)		0.050 (BSC)		
E	5.800	6.200	0.228	0.244	
E1	3.800	4.000	0.150	0.157	
L	0.400	1.270	0.016	0.050	
θ	0 °	8°	0 °	8°	



Note: 1.Controlling dimension: in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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